

MMBA812M6 PNP EPITAXIAL SILICON TRANSISTOR

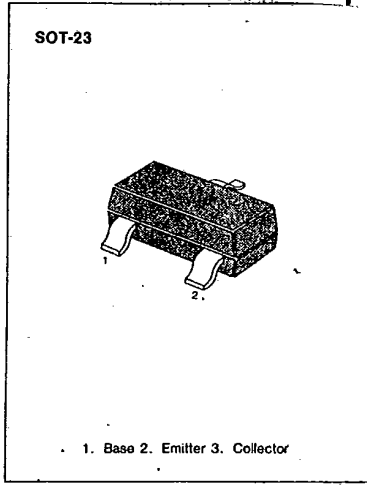
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GENERAL PURPOSE TRANSISTOR

ABSOLUTE MAXIMUM RATINGS (T_a = 25°C)

| Characteristic | Symbol | Rating | Unit |
|---------------------------|------------------|--------|------|
| Collector-Base Voltage | V _{CB0} | 50 | V |
| Collector-Emitter Voltage | V _{CE0} | 40 | V |
| Emitter-Base Voltage | V _{EB0} | 5 | V |
| Collector Current | I _C | 100 | mA |
| Collector Dissipation | P _C | 350 | mW |
| Storage Temperature | T _{stg} | 150 | °C |

• Refer to MMBT5086 for graphs



ELECTRICAL CHARACTERISTICS (T_a = 25°C)

| Characteristic | Symbol | Test Condition | Min | Max | Unit |
|--------------------------------------|-----------------------|---|-----|-----|------|
| Collector Cutoff Current | I _{CB0} | V _{CB} =40V, I _E =0 | | 100 | nA |
| Emitter Cutoff Current | I _{EB0} | V _{EB} =5V, I _C =0 | | 100 | nA |
| DC Current Gain | h _{FE} | V _{CE} =6V, I _C =1mA | 200 | 400 | |
| Collector-Emitter Saturation Voltage | V _{CE (sat)} | I _C =30mA, I _B =3mA | | 0.5 | V |
| Base-Emitter On Voltage | V _{BE (on)} | I _C =1mA, V _{CE} =6V | | 0.8 | V |

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Marking

